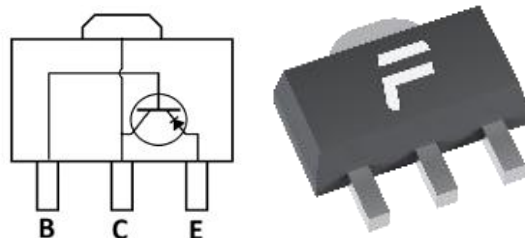


SOT-89-3L Bipolar Transistor 双极型三极管

■ Features 特点

PNP High Voltage Switching 高压开关
Low Equivalent On-Resistance 低等效电阻



■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V_{CBO}	-120	V
Collector-Emitter Voltage 集电极发射极电压	V_{CEO}	-100	V
Emitter-Base Voltage 发射极基极电压	V_{EBO}	-6	V
Collector Current 集电极电流	I_C	-2000	mA
Collector Current Pulse 集电极脉冲电流	I_{CP}	-3000	mA
Power dissipation 耗散功率	$P_C(T_a=25^{\circ}\text{C})$	500	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	250	$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^{\circ}\text{C}$	

■ Device Marking 产品打标

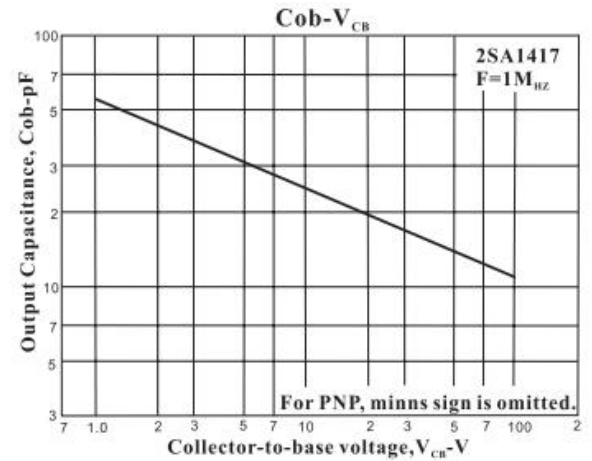
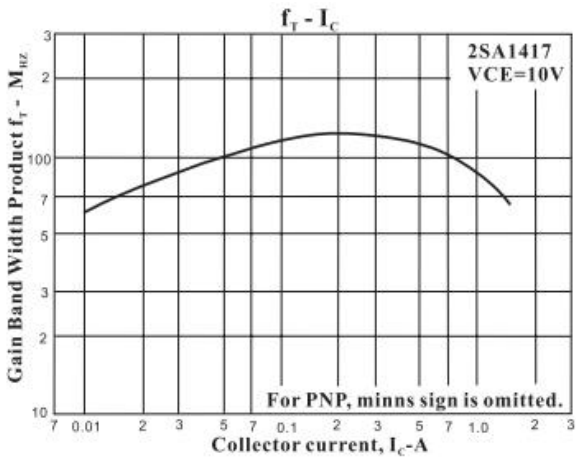
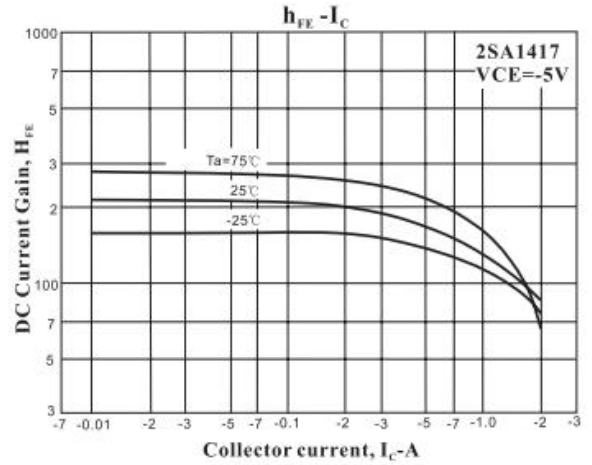
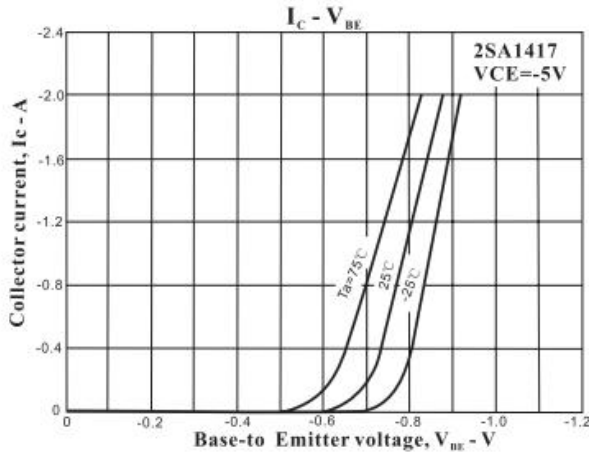
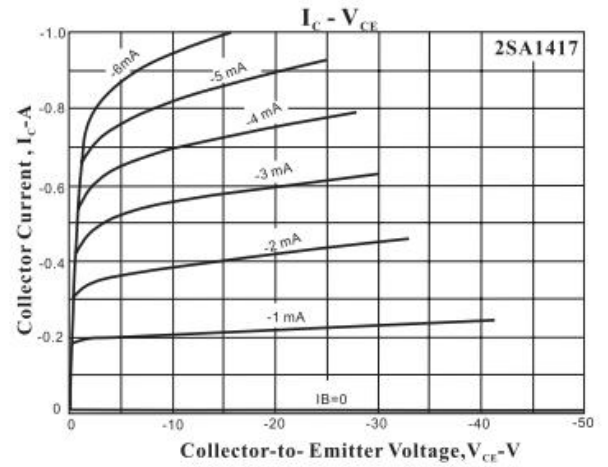
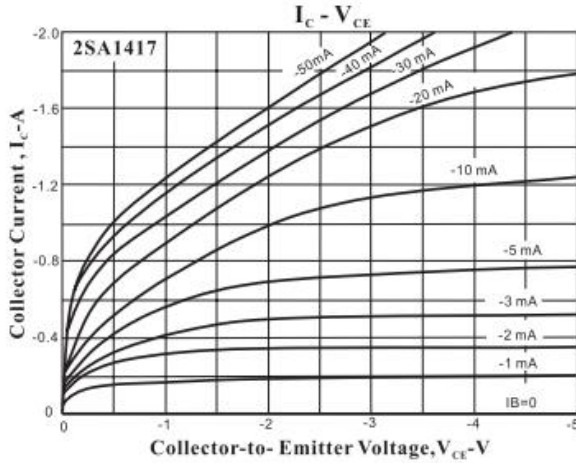
H_{FE}	100-200	140-280	200-400
Mark	ACR	ACS	ACT

■Electrical Characteristics 电特性

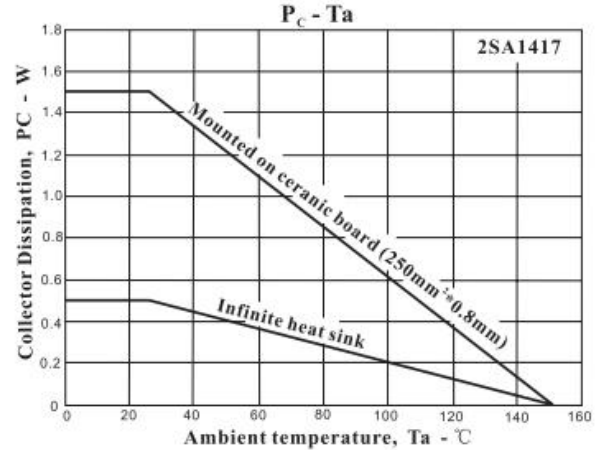
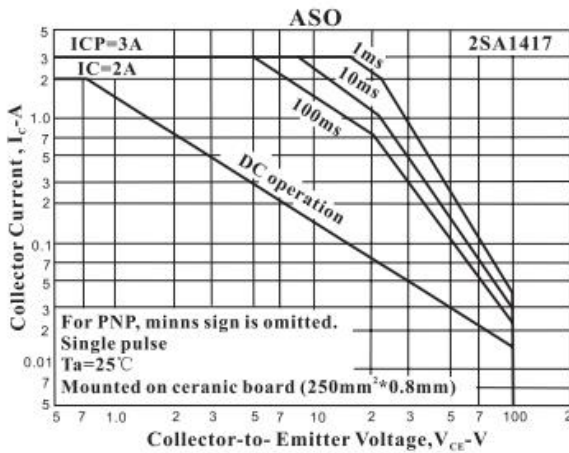
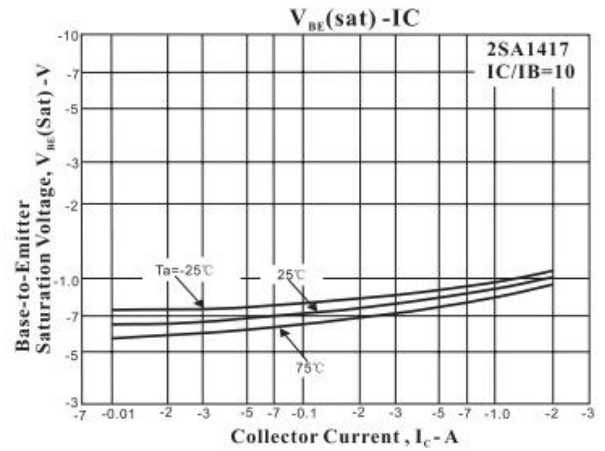
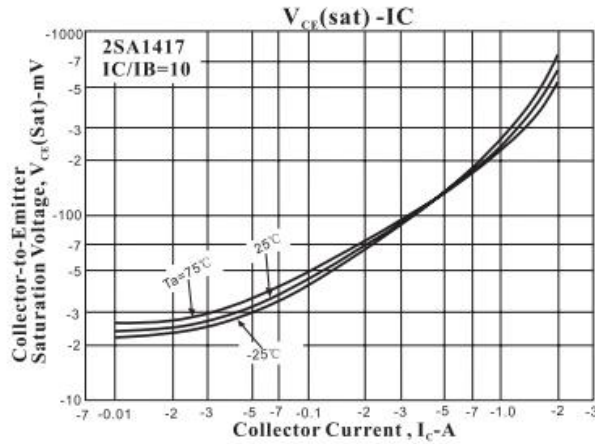
(TA=25℃ unless otherwise noted 如无特殊说明, 温度为 25℃)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压(IC= -100μA, IE=0)	BV _{CBO}	-120	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压(IC= -1mA, IB=0)	BV _{CEO}	-100	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压(IE= -100μA, IC=0)	BV _{EBO}	-6	—	—	V
Collector-Base Leakage Current 集电极基极漏电流(V _{CB} = -100V, IE=0)	I _{CBO}	—	—	-100	nA
Emitter-Base Leakage Current 发射极基极漏电流(V _{EB} = -4V, IC=0)	I _{EBO}	—	—	-100	nA
DC Current Gain 直流电流增益(V _{CE} = -5V, IC= -100mA)	H _{FE}	100	—	400	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降(IC= -1000mA, IB= -100mA)	V _{CE(sat)}	—	-220	-600	mV
Base-Emitter Saturation Voltage 基极发射极饱和压降(IC= -1000mA, IB= -100mA)	V _{BE(sat)}	—	-850	-1200	mV
Turn-on Time 开通时间 (V _{CC} = -50V, IC= -700mA, IB1= -IB2= -70mA)	t _{on}	—	80	—	ns
Storage Time 贮存时间 (V _{CC} = -50V, IC= -700mA, IB1= -IB2= -70mA)	t _s	—	750	—	ns
Fall Time 下降时间 (V _{CC} = -50V, IC= -700mA, IB1= -IB2= -70mA)	t _f	—	40	—	ns
Transition Frequency 特征频率(V _{CE} = -10V, IC= -100mA)	f _T	—	120	—	MHz
Output Capacitance 输出电容(V _{CB} = -10V, IE=0, f=1MHz)	C _{ob}	—	25	—	pF

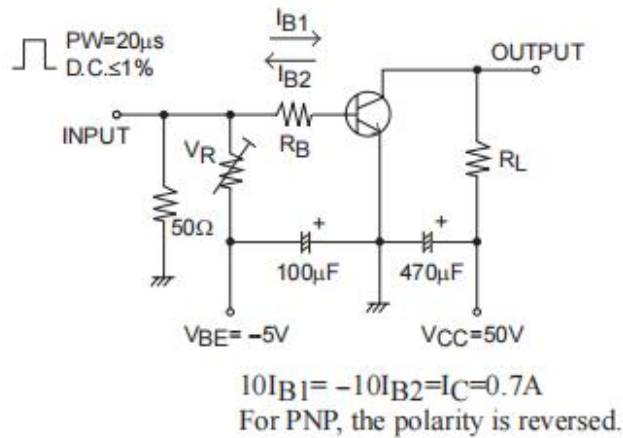
■ Typical Characteristic Curve 典型特性曲线



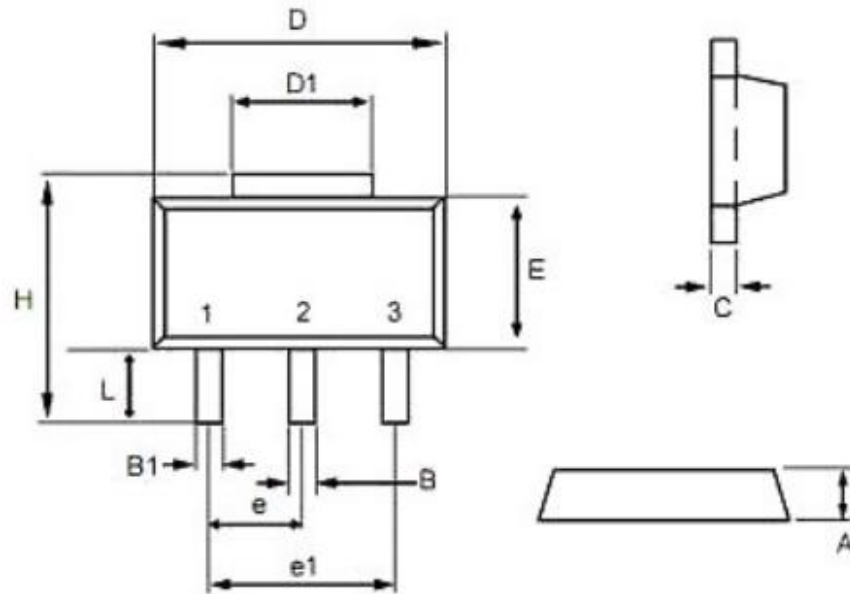
■ Typical Characteristic Curve 典型特性曲线



■ Test Circuit 测试电路



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.40	1.60	0.055	0.063
B	0.40	0.56	0.016	0.022
B1	0.35	0.48	0.014	0.019
C	0.35	0.44	0.014	0.017
D	4.40	4.60	0.173	0.181
D1	1.35	1.83	0.053	0.072
e	1.45	1.55	0.057	0.061
e1	2.95	3.05	0.116	0.120
E	2.29	2.60	0.090	0.102
H	3.75	4.25	0.148	0.167
L	0.80	1.20	0.031	0.047